

# UHF POWER LDMOS TRANSISTOR

**DESCRIPTION:**

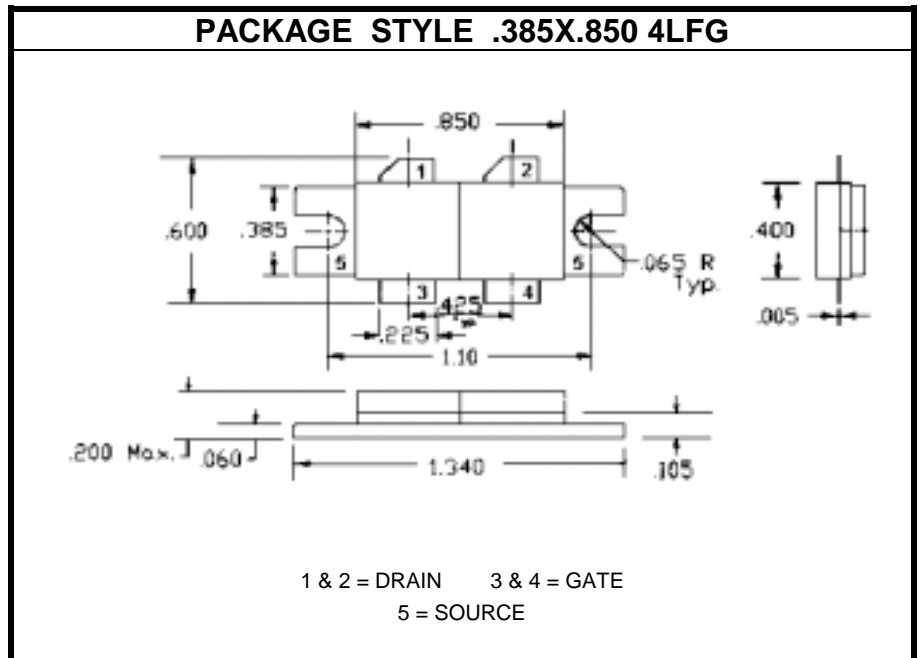
The **ASI BLF861A** is a Silicon N-channel enhancement mode lateral D-MOS push-pull transistor.

**FEATURES:**

- Internal input-output matching
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_D$	18 A
$V_{DS}$	65 V
$V_{GS}$	$\pm 15$ V
$P_{DISS}$	318 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	0.55 °C/W


**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{DSS}$	$I_D = 1.5$ mA	65			V
$I_{DSS}$	$V_{DS} = 32$ V $V_{GS} = 0$ V			2.2	$\mu$ A
$I_{DSX}$	$V_{DS} = 10$ V $V_{GS} = V_{GSth} + 9$ V	18			A
$I_{GSS}$	$V_{DS} = 0$ V $V_{GS} = \pm 15$ V			25	nA
$V_{GS(th)}$	$I_D = 150$ mA $V_{DS} = 10$ V	4.0		5.5	V
$R_{DS(on)}$	$I_D = 4.0$ A $V_{GS} = V_{GSth} + 9$ V		160		m $\Omega$
$g_{fs}$	$I_D = 4.0$ A $V_{DS} = 10$ V		4.0		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	$V_{DS} = 32$ V $V_{GS} = 0$ V $f = 1.0$ MHz		82 40 6.0		pF
$G_p$ $\eta_D$	$V_{DS} = 32$ V $P_{out} = 150$ W $f = 860$ MHz	13.5 50	14.5		dB %